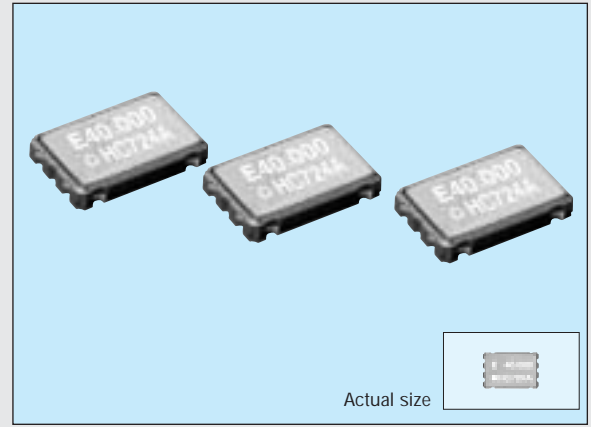


HIGH-FREQUENCY CRYSTAL OSCILLATOR

SG-710 series

Product number (please refer to page 1)
Q33710xxxxxx00

- Ceramic package with 1.5 mm thickness.
- Excellent environmental capability.
- Low current consumption due to use of C-MOS technology.
- Low current consumption by output enable function (OE) or standby function (ST).



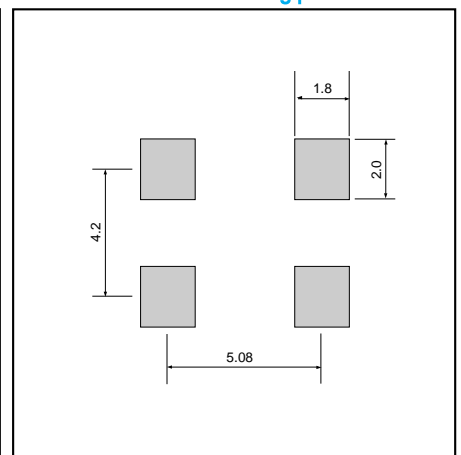
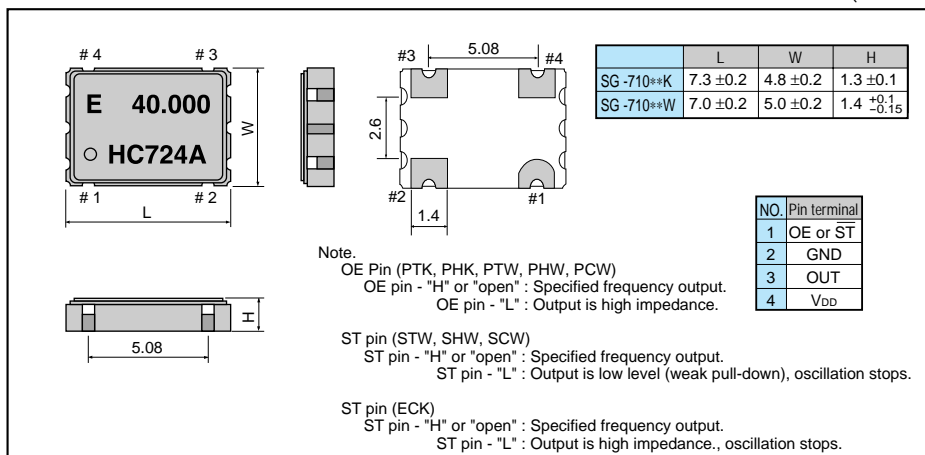
Specifications (characteristics)

| Item | Symbol | Specifications | | | Remarks | |
|-------------------------------------|-----------------------|--|---------------------------|---------------------------|---|--|
| | | SG-710PTK | SG-710PHK | SG-710ECK | | |
| Output frequency range | f_0 | 1.8000 MHz to 50.0000 MHz | 1.8000 MHz to 80.0000 MHz | 1.8000 MHz to 67.0000 MHz | Refer to page 31. "Frequency range" | |
| Power source voltage | Max. supply voltage | V_{DD-GND} | | -0.5 V to +7.0 V | | |
| | Operating voltage | V_{DD} | | 5.0 V \pm 0.5 V | 3.3 V \pm 0.3 V | |
| Temperature range | Storage temperature | T_{STG} | | | -55 °C to +125 °C | Stored as bare product after unpacking |
| | Operating temperature | T_{OPR} | | | -10 °C to +70 °C (-40 °C to +85 °C) | Refer to page 31. "Frequency range" |
| Frequency stability | $\Delta f/f_0$ | B: $\pm 50 \times 10^{-6}$ C: $\pm 100 \times 10^{-6}$ M: $\pm 100 \times 10^{-6}$ | | | B, C: -10 °C to +70 °C, M: -40 °C to +85 °C | |
| Current consumption | I_{OP} | 13 mA Max. | | 15 mA Max. | 8 mA Max. | $F_0 \leq 25$ MHz, No load condition (ECK: $F_0 \leq 32$ MHz, No load condition) |
| | | 24 mA Max. | | 26 mA Max. | 15 mA Max. | $F_0 \leq 50$ MHz, No load condition |
| | | — | | 34 mA Max. | 18 mA Max. | $F_0 \leq 67$ MHz, No load condition |
| | | — | | 40 mA Max. | — | $F_0 \leq 80$ MHz, No load condition |
| Output disable current | I_{OE} | 6 mA Max. | | 5 mA Max. | — | $F_0 \leq 25$ MHz, OE=GND(PTK, PHK) |
| | | 12 mA Max. | | 10 mA Max. | — | $F_0 \leq 50$ MHz, OE=GND(PTK, PHK) |
| | | — | | 13 mA Max. | — | $F_0 \leq 67$ MHz, OE=GND(PTK, PHK) |
| | | — | | 16 mA Max. | — | $F_0 \leq 80$ MHz, OE=GND(PTK, PHK) |
| Standby current | I_{ST} | — | | 10 μ A Max. | ST=GND(ECK) | |
| Duty | t_w/t | — | | 45 % to 55 % | 40 % to 60 % | CMOS load: 1/2 V_{DD} level |
| | | 45 % to 55 % | | 40 % to 60 % | — | TTL load: 1.4 V level |
| High output voltage | V_{OH} | 2.4 V Min. | $V_{DD} - 0.5$ V Min. | 0.9 x V_{DD} Min. | $I_{OH} = -16$ mA(PTK,PHK), -2 mA(ECK) | |
| Low output voltage | V_{OL} | 0.4 V Max. | 0.5 V Max. | 0.1 x V_{DD} Max. | $I_{OL} = 16$ mA(PTK,PHK), 2 mA(ECK) | |
| Output load condition (fan out) | TTL | N | 10 TTL Max. | 10 TTL Max. | — | |
| | CMOS | C_L | (15 pF Max.) | 50 pF Max. | 15 pF Max. | |
| Output enable/disable input voltage | V_{IH} | 2.0 V Min. | | 0.7 x V_{DD} Min. | OE terminal(PTK,PHK) | |
| | V_{IL} | 0.8 V Max. | | 0.3 x V_{DD} Max. | ST terminal(ECK) | |
| Output rise time | t_{rHL} | — | | 5 ns Max. | 6 ns Max. | CMOS load: 10 % \rightarrow 90 % V_{DD} |
| | | 5 ns Max. | | — | — | TTL load: 0.4 V \rightarrow 2.4 V |
| Output fall time | t_{fHL} | — | | 5 ns Max. | 6 ns Max. | CMOS load: 90 % \rightarrow 10 % V_{DD} |
| | | 5 ns Max. | | — | — | TTL load: 2.4 V \rightarrow 0.4 V |
| Oscillation start up time | t_{OSC} | — | | 10 ms Max. | Time at minimum operating voltage to be 0 s | |
| Aging | f_a | — | | | $\pm 5 \times 10^{-6}$ /year Max. | $T_a = +25$ °C, $V_{DD} = 5.0$ V/3.3 V, First year |
| Shock resistance | S.R. | — | | | $\pm 10 \times 10^{-6}$ Max. | Three drops on a hard board from 750 mm or excitation test with 29400 m/s ² x 0.3 ms x 1/2sine wave in 3 directions |

External dimensions

(Unit: mm)

Recommended soldering pattern (Unit: mm)



■ Specifications (characteristics)

| Item | Symbol | Specifications | | | Remarks | |
|-------------------------------------|-----------------------|--|---------------|-----------------------------|---|-------------------------------|
| | | SG-710PTW/STW | SG-710PHW/SHW | SG-710PCW/SCW | | |
| Output frequency range | fo | 80.0001 MHz to 135.0000 MHz | 135.0000 MHz | 67.0001 MHz to 135.0000 MHz | Refer to page 31. "Frequency range" | |
| Power source voltage | Max. supply voltage | -0.5 V to +7.0 V | | | | |
| | Operating voltage | 5.0 V ±0.5 V | | | 3.3 V ±0.3 V | |
| Temperature range | Storage temperature | -55 °C to +125 °C | | | Stored as bare product after unpacking | |
| | Operating temperature | -20 °C to +70 °C | | -40 °C to +85 °C | Refer to page 31. "Frequency range" | |
| Frequency stability | Δf/fo | B : ±50 x 10 ⁻⁶ C : ±100 x 10 ⁻⁶ | | | -20 °C to +70 °C | |
| | | | | M : ±100 x 10 ⁻⁶ | -40 °C to +80 °C | |
| Current consumption | I _{OP} | 45 mA Max. | | 28 mA Max. | No load condition (fo = Max.) | |
| Output disable current | I _{OE} | 30 mA Max. | | 16 mA Max. | OE=GND(P*W) | |
| Standby current | I _{ST} | 50 μA Max. | | | ST=GND(S*W) | |
| Duty | CMOS level | — | | | 40 % to 60 % | CMOS load: 1/2V _{DD} |
| | TTL level | 40 % to 60 % | | — | — | TTL load: 1.4 V |
| Output voltage | V _{OH} | V _{DD} -0.4 V Min. | | | I _{OH} = -16 mA (*TW/HW)/-8 mA(*CW) | |
| | V _{OL} | 0.4 V Max. | | | I _{OL} = 16 mA (*TW/HW)/8 mA(*CW) | |
| Output load condition (fan out) | CL | 15 pF | — | | fo ≤ 135 MHz | |
| | | 5 TTL + 15 pF | — | | fo ≤ 90 MHz | |
| | | — | 15 pF | 15 pF | fo ≤ 135 MHz | |
| | | — | 25 pF | — | fo ≤ 125 MHz | |
| Output enable disable input voltage | V _{IH} | 2.0 V Min. | | 70 % V _{DD} Min. | OE, ST | |
| | V _{IL} | 0.8 V Max. | | 20 % V _{DD} Max. | OE, ST | |
| Output rise time | t _{RLH} | 2.0 ns Max. | — | | TTL load: 0.8 V→2.0 V, CL = Max. | |
| | | 4.0 ns Max. | — | | TTL load: 0.4 V→2.4 V, CL = Max. | |
| | | — | 3.0 ns Max. | 3.0 ns Max. | CMOS load: 20 % V _{DD} →80 % V _{DD} , CL = Max. | |
| Output fall time | t _{THL} | 2.0 ns Max. | — | | TTL load: 2.0 V→0.8 V, CL = Max. | |
| | | 4.0 ns Max. | — | | TTL load: 2.4 V→0.4 V, CL = Max. | |
| | | — | 3.0 ns Max. | 3.0 ns Max. | CMOS load: 80 % V _{DD} →20 % V _{DD} , CL = Max. | |
| Oscillation start up time | t _{OSC} | 10 ms Max. | | | Time at minimum operating voltage to be 0 s | |
| Aging | fa | ±5 x 10 ⁻⁶ /year Max. | | | Ta=+25 °C, V _{DD} =5.0 V / 3.0 V, First year | |
| Shock resistance | S.R. | ±20 x 10 ⁻⁶ Max. | | | Three drops on a hard board from 750 mm or excitation test with 29400 m/s ² x 0.3 ms x 1/2 sine wave in 3 directions | |